D1_{D2}D2



Description

The DMP3085LSD-13 uses advanced trench technology and design to provide excellent RDS(ON) with low gate charge. It can be used in a wide variety of applications.

General Features

 $V_{DS} = -30V, I_{D} = -5.3A$

 $R_{DS(ON)}$ < 42m Ω @ V_{GS} =-10V

 $R_{DS(ON)}$ < 85m Ω @ V_{GS} =-4.5V

D1 D1 D2 D2 80 70 60 50

SOP-8 (SOIC-8)

Application

PWM application

Load switch

Dual P-Channel MOSFET

Package Marking and Ordering Information

Product ID	Pack	Brand	Qty(PCS)
DMP3085LSD-13	SOP-8(SOIC-8)	HXY MOSFET	3000

Absolute Maximum Ratings (T_A=25[°]C unless otherwise noted)

Symbol	Parameter	Limit	Unit
V _{DS}	Drain-Source Voltage	-30	V
V _G s	Gate-Source Voltage	±20	V
I _D	Drain Current-Continuous	-5.3	А
Ірм	Drain Current-Pulsed (Note 1)	-20	А
P _D	Maximum Power Dissipation	2.6	W
T _J ,T _{STG}	Operating Junction and Storage Temperature Range	-55 To 150	°C
Reja	Thermal Resistance, Junction-to-Ambient (Note 2)	49	°C/W



Electrical Characteristics (T_A=25° unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =-250μA	-30	-33	-	V
Zero Gate Voltage Drain Current	IDSS	V _{DS} =-24V,V _{GS} =0V	-		-1	μΑ
Gate-Body Leakage Current	Igss	V _{GS} =±20V,V _{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =-250µA	-1	-1.6	-3	V
	Rds(on)	V _{GS} =-10V, I _D =-5.3A	-	35	42	mR
Drain-Source On-State Resistance		V _{GS} =-4.5V, I _D =-4.2A	-	70	85	mR
Forward Transconductance	grs	V _{DS} =-15V, I _D =-4.5A	4	7	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	Clss		-	540	-	PF
Output Capacitance	Coss	V _{DS} =-15V,V _{GS} =0V,	-	150	-	PF
Reverse Transfer Capacitance	Crss	F=1.0MHz	-	75	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	td(on)		-	8	-	nS
Turn-on Rise Time	tr	V _{DD} =-15V, ID=-1A,	-	14	-	nS
Turn-Off Delay Time	t _{d(off)}	V _{GS} =-10V,R _{GEN} =6	-	18	-	nS
Turn-Off Fall Time	t _f		-	10	-	nS
Total Gate Charge	Qg		-	12	-	nC
Gate-Source Charge	Qgs	V _{DS} =-15V,I _D =-5.3A,V _{GS} =-	-	2.4	-	nC
Gate-Drain Charge	Q _{gd}	100	-	3.2	-	nC
Drain-Source Diode Characteristics		1			l	
Diode Forward Voltage (Note 3)	Vsp	V _{GS} =0V, I _S =-5.3A	_	-	-1.2	V

Notes:

- $\textbf{1.} \ \textbf{Repetitive Rating: Pulse width limited by maximum junction temperature.}$
- **2.** Surface Mounted on FR4 Board, $t \le 10$ sec.
- **3.** Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2%.
- 4. Guaranteed by design, not subject to production



Typical Electrical and Thermal Characteristics

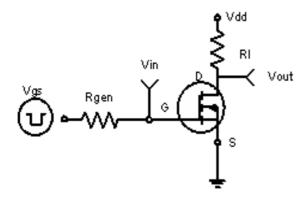
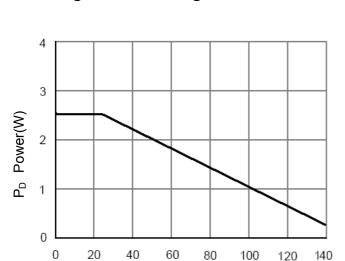


Figure 1:Switching Test Circuit



 T_J -Junction Temperature (°C) **Figure 3 Power Dissipation**

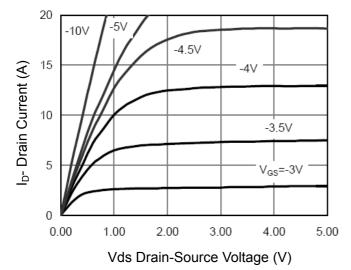


Figure 5 Output Characteristics

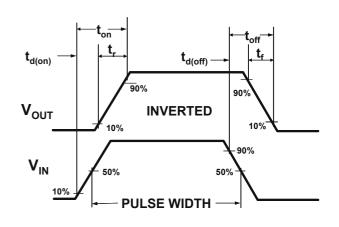


Figure 2:Switching Waveforms

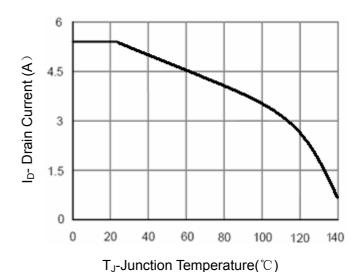


Figure 4 Drain Current

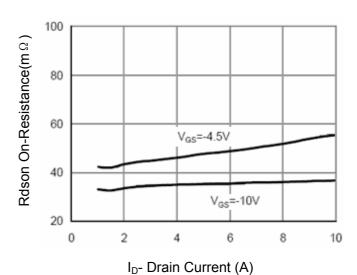


Figure 6 Drain-Source On-Resistance

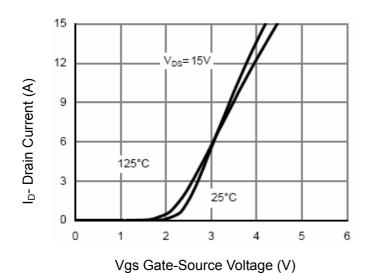
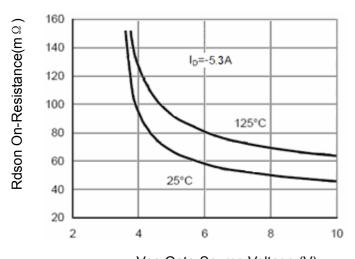


Figure 7 Transfer Characteristics



Vgs Gate-Source Voltage (V)
Figure 9 Rdson vs Vgs

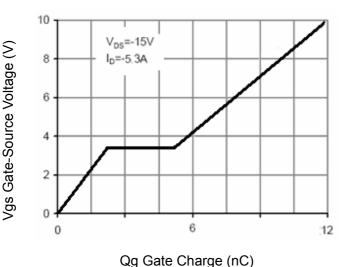


Figure 11 Gate Charge

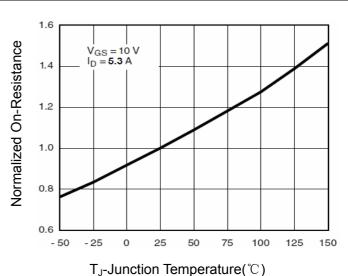


Figure 8 Drain-Source On-Resistance

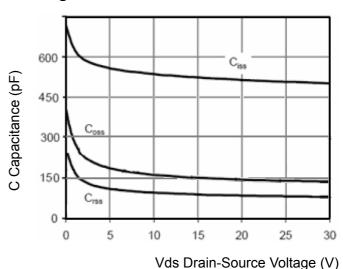
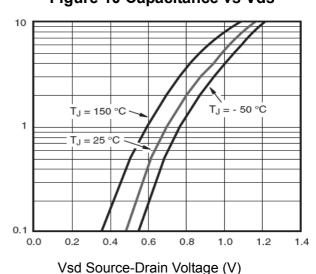


Figure 10 Capacitance vs Vds



Is- Reverse Drain Current (A)

Figure 12 Source- Drain Diode Forward

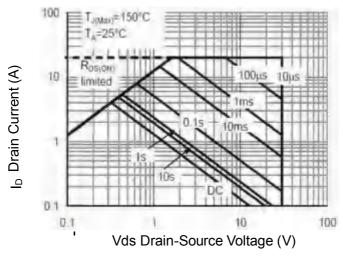
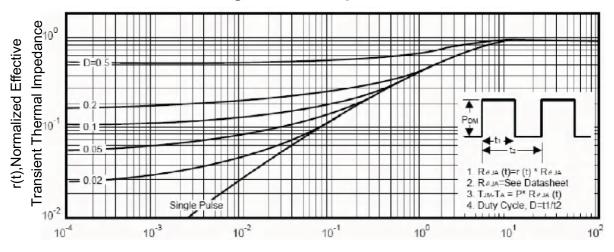


Figure 13 Safe Operation Area

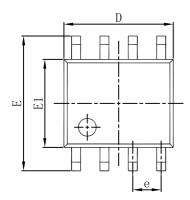


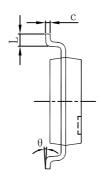
Square Wave Pluse Duration(sec)

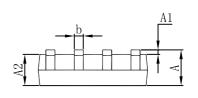
Figure 14 Normalized Maximum Transient Thermal Impedance



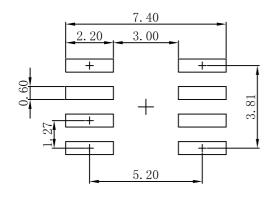
SOP-8(SOIC-8) Package Outline Dimensions







Symbol	Dimensions In Millimeters		Dimensions In Inches		
	Min	Max	Min	Max	
A	1. 350	1.750	0.053	0.069	
A1	0.100	0. 250	0.004	0.010	
A2	1.350	1.550	0.053	0.061	
b	0.330	0.510	0.013	0.020	
c	0.170	0.250	0.007	0.010	
D	4.800	5.000	0.189	0. 197	
e	1.270 (BSC)		0.050 (BSC)		
E	5.800	6. 200	0. 228	0. 244	
E1	3.800	4.000	0.150	0. 157	
L	0.400	1.270	0.016	0.050	
θ	0°	8°	0°	8°	



- Note:
 1.Controlling dimension: in millimeters.
- 2.General tolerance:± 0.05mm.
 3.The pad layout is for reference purposes only.

Dual P-Channel Enhancement Mode MOSFET

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